华润微电子（重庆）有限公司

CRSM080N10L2

SkyMOS2 N-MOSFET 100V, 6.8mΩ, 71A

Features

- Uses CRM(CQ) advanced SkyMOS2 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent Q_gx$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria
- Typical ESD (HBM): 500 V

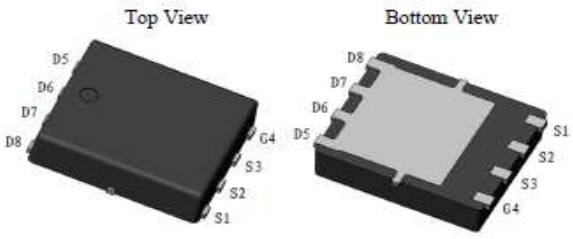
Product Summary

V_{DS}	100V
$R_{DS(on)@10V\ typ}$	6.8mΩ
$R_{DS(on)@4.5V\ typ}$	8.3mΩ
I_D	71A

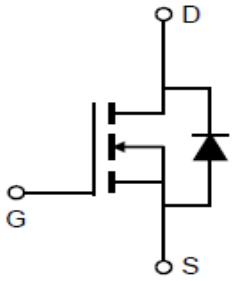
Applications

- Synchronous Rectification for AC/DC Quick Charger
- Battery management
- UPS (Uninterrupible Power Supplies)

100% Avalanche Tested



CRSM080N10L2



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSM080N10L2	-	DFN5X6	Tape&Reel	N/A	N/A	5000pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	100	V
Continuous drain current T_C = 25°C (Silicon limit) T_C = 25°C (Package limit) T_C = 100°C (Silicon limit)	I_D	 71 80 45	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	284	A
Avalanche energy, single pulse (L=0.3mH, Rg=25Ω)	E_{AS}	101	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	79	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

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Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	1.58	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	47.0	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	100	115	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	1.4	1.8	2.2	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=100V,V_{GS}=0V T_j=25°C
		-	-	10		T_j=125°C
Gate-source leakage current	I_{GSS}	-	-	±100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$		6.8	8.2	mΩ	VGS=10V,I_D=30A
		-	8.3	10.4	mΩ	VGS=4.5V,I_D=30A
Transconductance	g_{fs}	-	91	-	S	V_{DS}=5V,I_D=30A
Dynamic Characteristic						
Input Capacitance	C_{iss}	1313	2626	3939	pF	V_{GS}=0V, V_{DS}=50V, f=1MHz
Output Capacitance	C_{oss}	228.5	457	685.5		
Reverse Transfer Capacitance	C_{rss}	19	38	76		
Gate Total Charge	Q_G	22.25	44.5	66.75	nC	V_{GS}=10V, V_{DS}=50V, I_D=50A, f=1MHz
Gate-Source charge	Q_{gs}	5.2	10.4	15.6		
Gate-Drain charge	Q_{gd}	3.4	6.8	10.2		
Turn-on delay time	$t_{d(on)}$	-	10.3	15.45	ns	V_{GS}=10V, V_{DD}=50V, R_{G_ext}=3.0Ω
Rise time	t_r	-	62	93		
Turn-off delay time	$t_{d(off)}$	-	30	45		
Fall time	t_f	-	98	147		
Gate resistance	R_G	-	1.1	1.65	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

Body Diode Characteristic

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Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.86	1.2	V	V_{GS}=0V,I_{SD}=30A
Body Diode Reverse Recovery Time	t_{rr}	-	64	96	ns	I_F=50A, dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	-	101	151.5	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

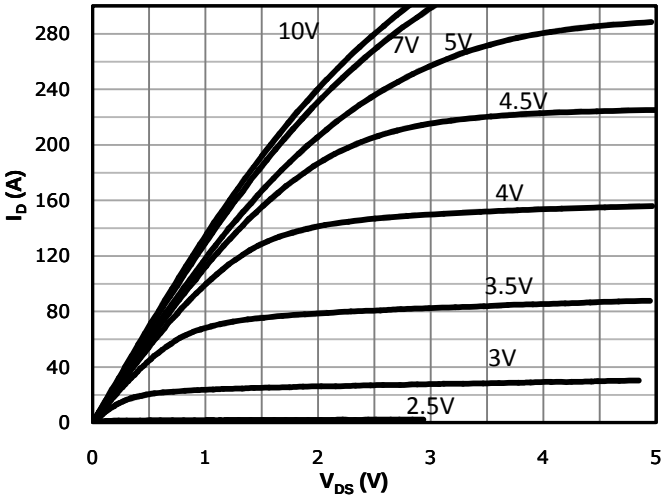
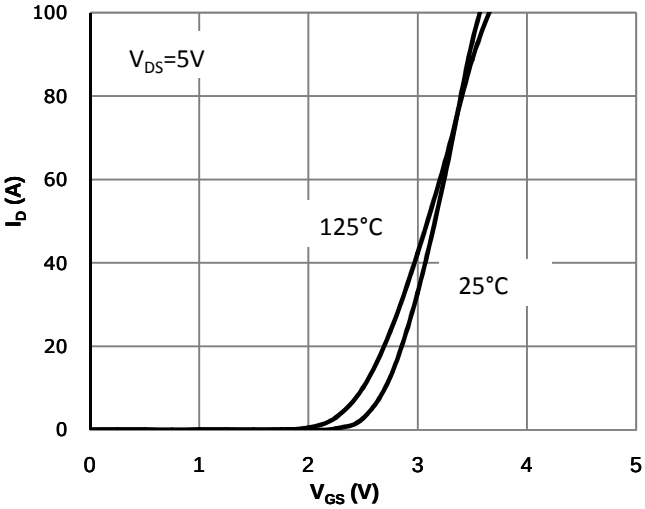


Fig 2: Transfer Characteristics



3: Rds(on) vs Drain Current and Gate Voltage

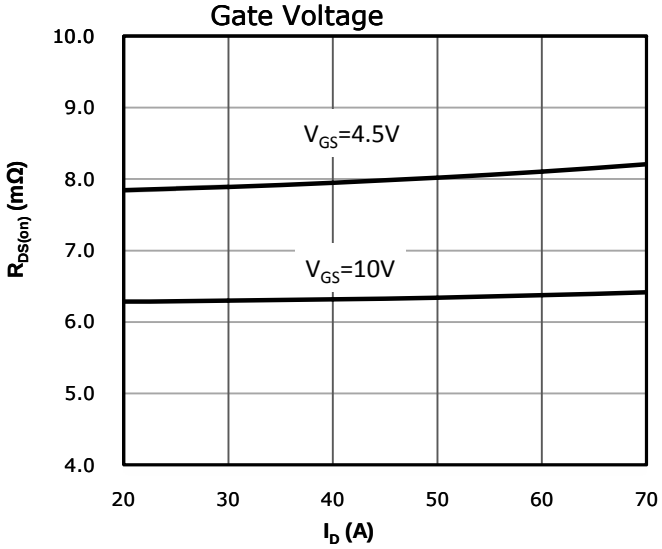


Fig 4: Rds(on) vs Gate Voltage

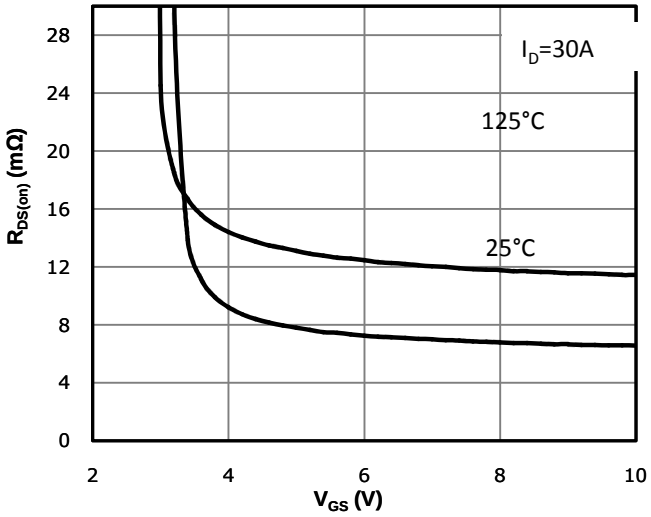


Fig 5: Rds(on) vs. Temperature

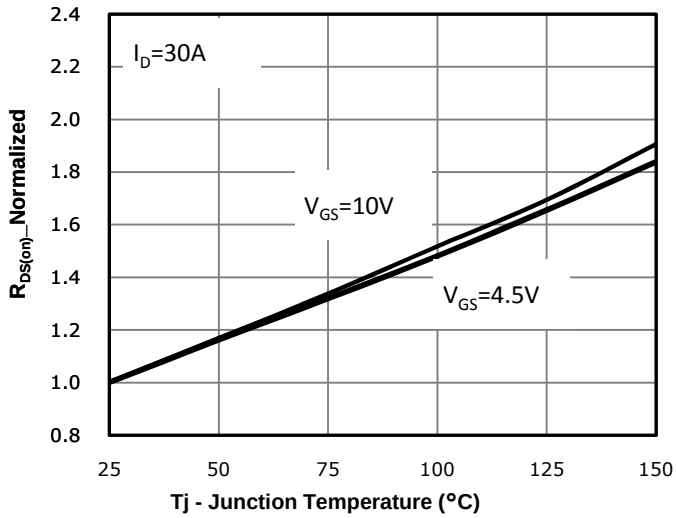


Fig 6: Capacitance Characteristics

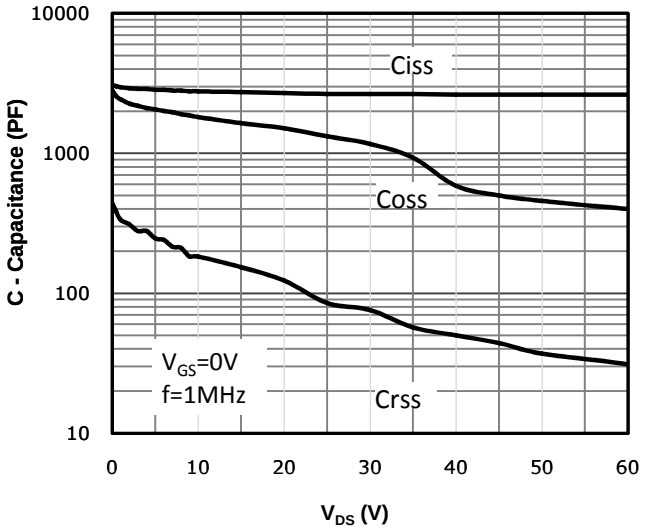


Fig 7: Gate Charge Characteristics

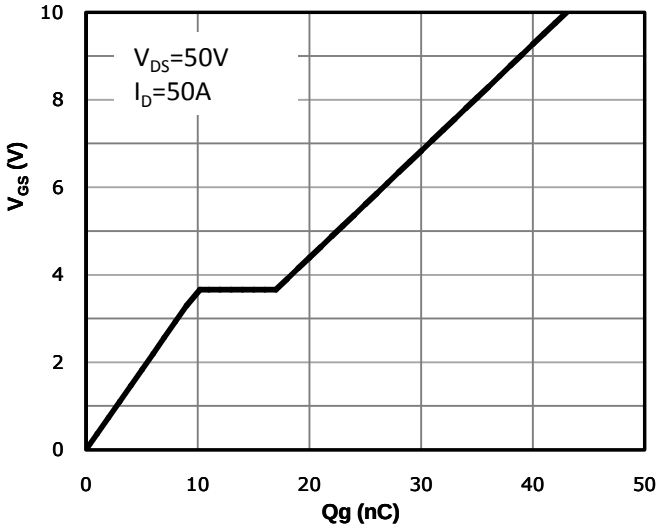


Fig 8: Body-diode Forward Characteristics

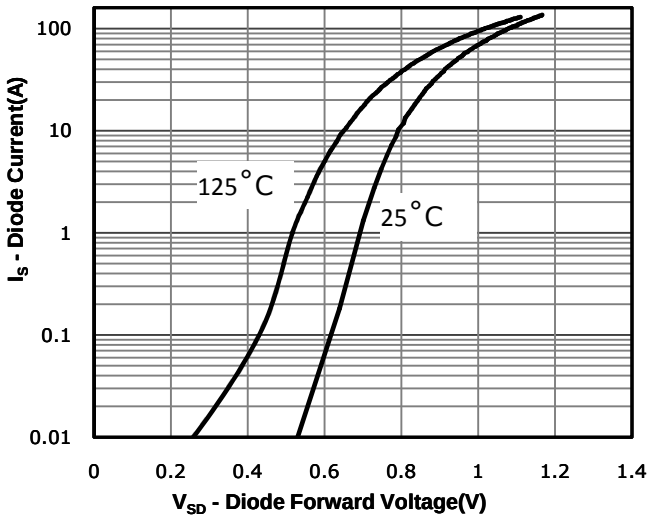


Fig 9: Power Dissipation

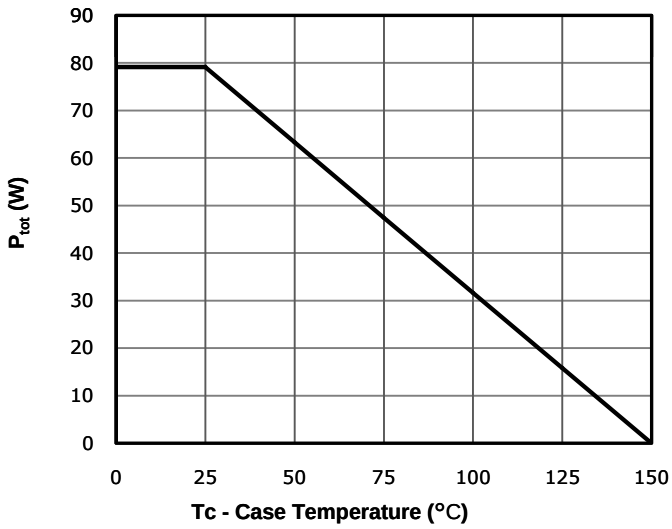


Fig 10: Drain Current Derating

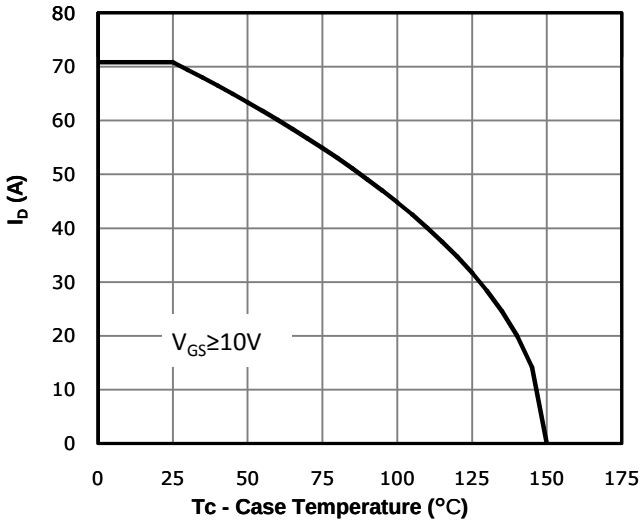


Fig 11: Safe Operating Area

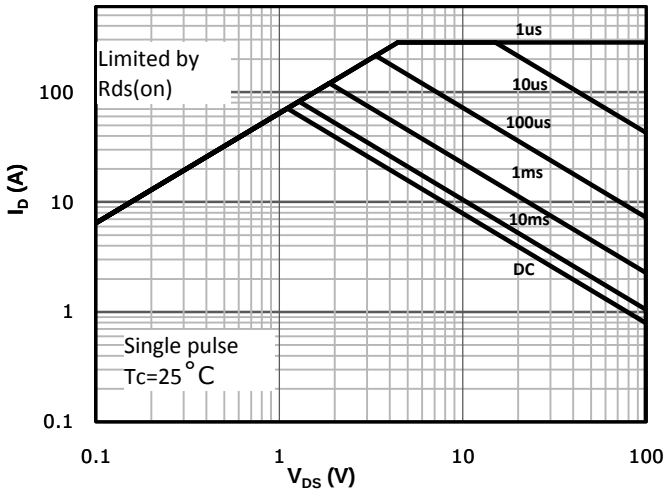
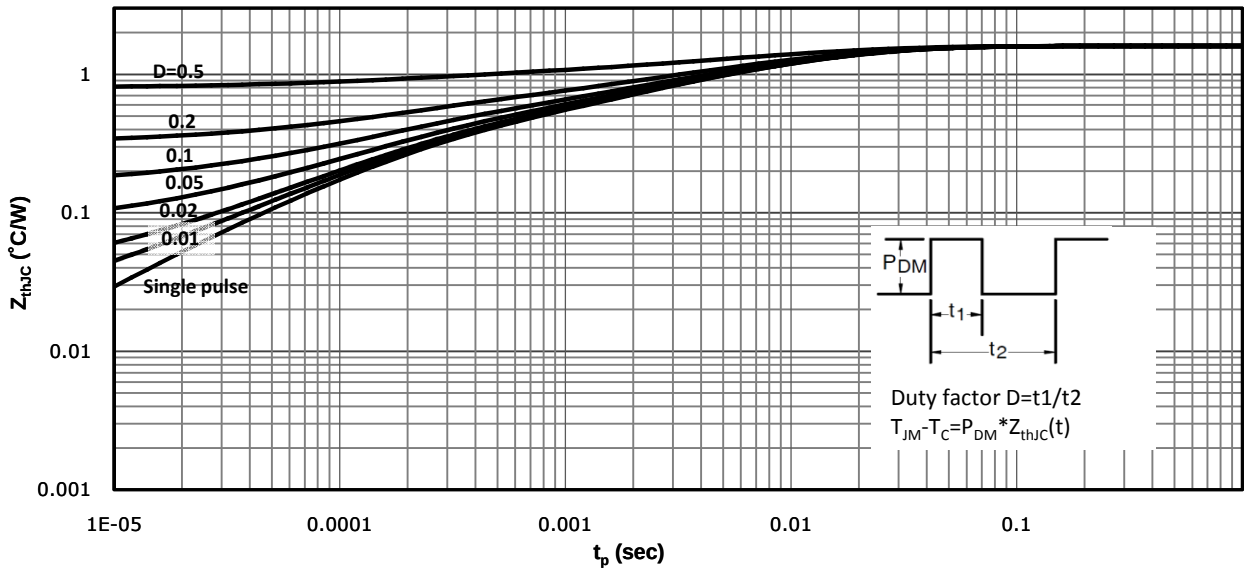
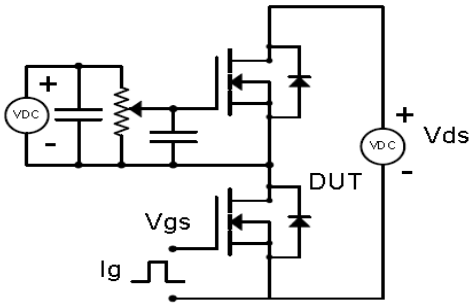


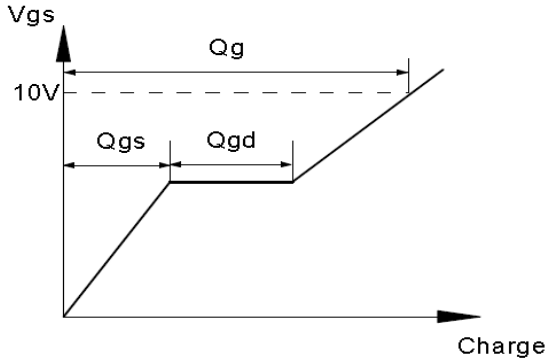
Fig 12: Max. Transient Thermal Impedance



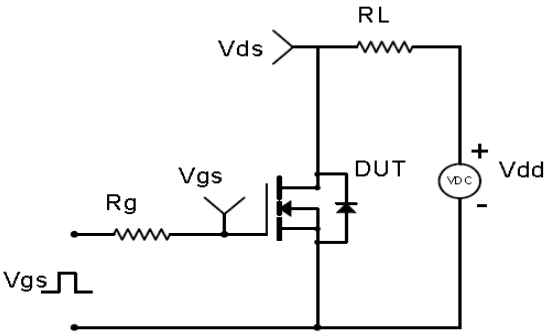
Test Circuit & Waveform

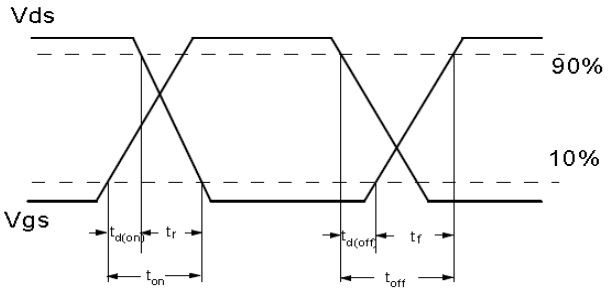
Gate Charge Test Circuit & Waveform



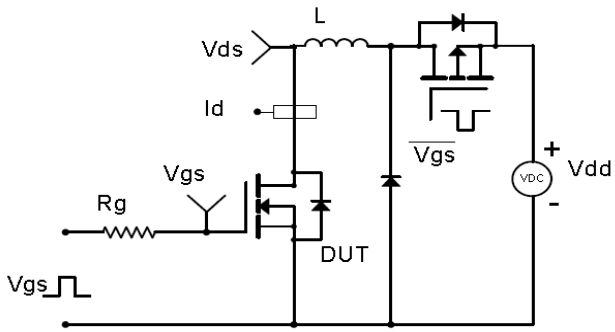


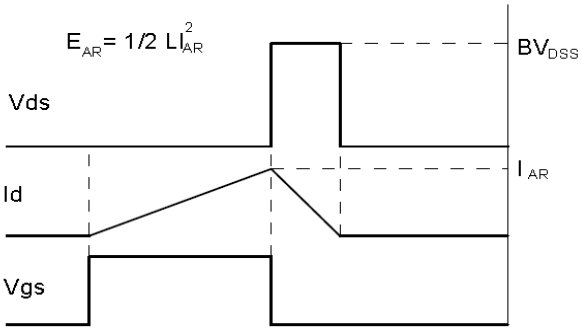
Resistive Switching Test Circuit & Waveforms



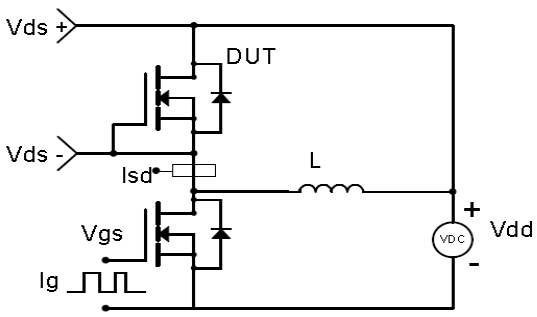


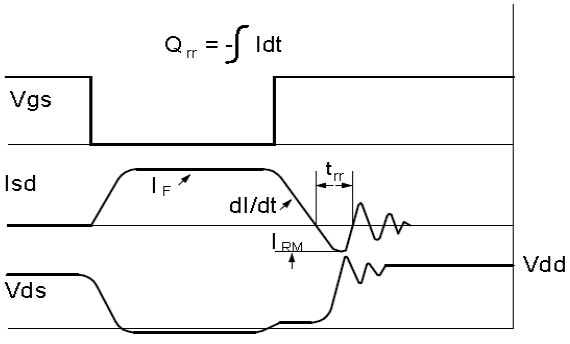
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



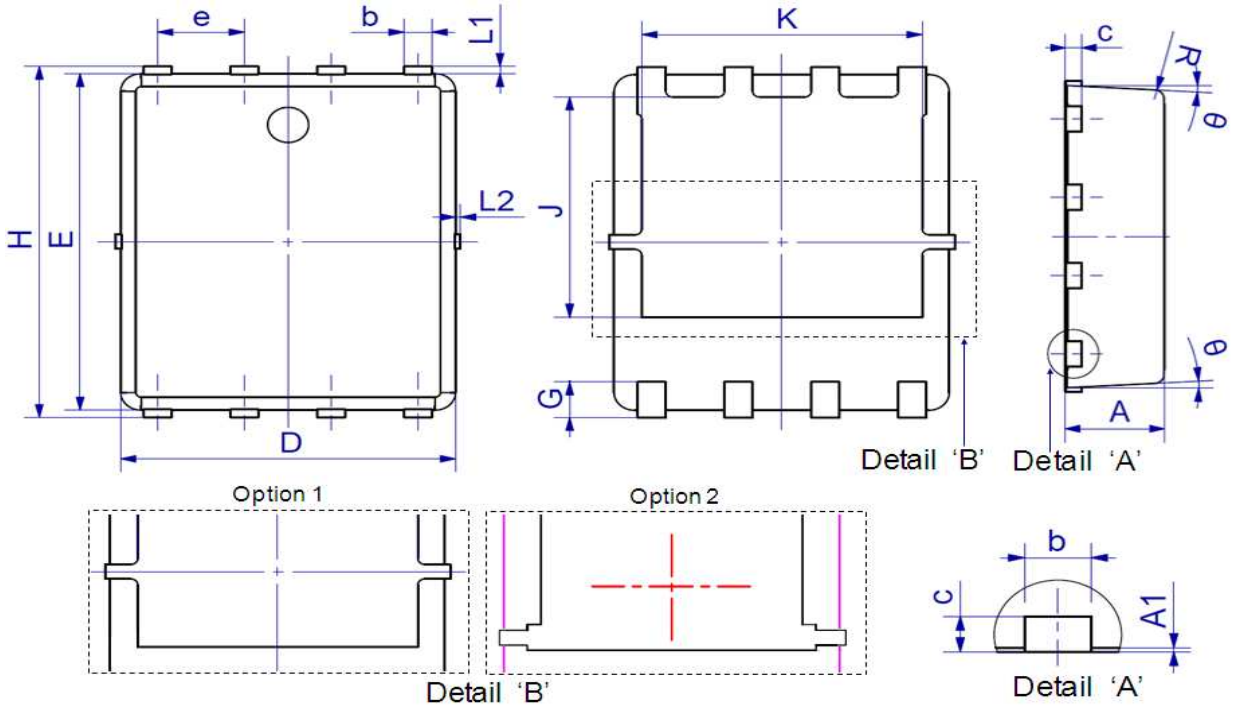


Diode Recovery Test Circuit & Waveforms





Package Outline: DFN5X6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.80	1.20	0.031	0.047
A1	0.00	0.05	0.000	0.002
b	0.30	0.51	0.012	0.020
c	0.15	0.35	0.006	0.014
D	4.80	5.40	0.189	0.213
e	1.27 BSC		0.050 BSC	
E	5.66	6.06	0.223	0.239
G	0.30	0.71	0.012	0.028
H	5.90	6.35	0.232	0.250
J	3.32	3.92	0.131	0.154
K	3.61	4.25	0.142	0.167
L1	0.05	0.25	0.002	0.010
L2	0.00	0.15	0.000	0.006
R	0.25 REF		0.010 REF	
θ	0°	12°	0°	12°

Revision History

Revison	Date	Major changes
1.0	2018-9-11	Release of formal version.
2.0	2019-1-30	Revise Rdson spec& outline size

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.